

n-Channel Power MOSFET

OptiMOS™
BSB165N15NZ3 G

Data Sheet

2.2, 2011-07-20
Final

Industrial & Multimarket

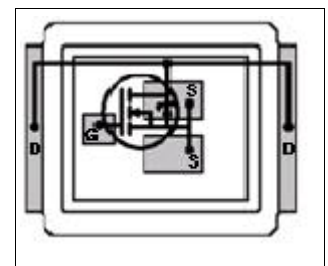
1 Description

OptiMOS™150V products are class leading power MOSFETs for highest power density and energy efficient solutions. Ultra low gate- and output charges together with lowest on state resistance in small footprint packages make OptiMOS™ 150V the best choice for the demanding requirements of voltage regulator solutions in Solar, Drives, Datacom and Telecom applications. Super fast switching Control FETs together with low EMI Sync FETs provide solutions that are easy to design in. OptiMOS™ products are available in high performance packages to tackle your most challenging applications giving full flexibility in optimizing space, efficiency and cost.



Features

- Optimized for high switching frequency DC/DC converter
- Very low on-resistance $R_{DS(on)}$
- Excellent gate charge x $R_{DS(on)}$ product (FOM)
- Pb-free plating; RoHS compliant
- Halogen-free according to IEC61249-2-21
- Double sided cooling
- Compatible with DirectFET® package MZ footprint and outline
- Low parasitic inductance
- Low profile (<0.7 mm)



Applications

- Synchronous rectification
- Primary side switches
- Power management for high performance computing
- High power density point of load converters



Table 1 Key Performance Parameters

| Parameter | Value | Unit | Related Links |
|------------------|-------|------|--|
| V_{DS} | 150 | V | IFX OptiMOS webpage IFX OptiMOS product brief IFX OptiMOS spice models IFX Design tools |
| $R_{DS(on),max}$ | 16.5 | mΩ | |
| I_D | 45 | A | |
| Q_{OSS} | 68 | nC | |
| $Q_{g,typ}$ | 26 | | |

| Type | Package | Marking |
|----------------|-----------|---------|
| BSB165N15NZ3 G | MG-WDSO-2 | 0115 |

2 Maximum ratings

at $T_j = 25\text{ °C}$, unless otherwise specified.

Table 2 Maximum ratings

| Parameter | Symbol | Values | | | Unit | Note / Test Condition |
|-------------------------------------|----------------|-----------|------|------|------|---|
| | | Min. | Typ. | Max. | | |
| Continuous drain current | I_D | - | - | 45 | A | $V_{GS}=10\text{ V}, T_C=25\text{ °C}$ |
| | | - | - | 29 | | $V_{GS}=10\text{ V}, T_C=100\text{ °C}$ |
| | | - | - | 9 | | $V_{GS}=10\text{ V}, T_A=25\text{ °C}, R_{thJA}=45\text{ K/W}^{1)}$ |
| Pulsed drain current ²⁾ | $I_{D,pulse}$ | - | - | 180 | | $T_C=25\text{ °C}$ |
| Avalanche energy, single pulse | E_{AS} | - | - | 440 | mJ | $I_D=30\text{ A}, R_{GS}=25\text{ }\Omega$ |
| Gate source voltage | V_{GS} | -20 | - | 20 | V | |
| Power dissipation | P_{tot} | - | - | 78 | W | $T_C=25\text{ °C}$ |
| | | - | - | 2.8 | | $T_A=25\text{ °C}, R_{thJA}=45\text{ K/W}^{1)}$ |
| Operating and storage temperature | T_j, T_{stg} | -40 | - | 150 | °C | |
| IEC climatic category; DIN IEC 68-1 | | 55/150/56 | | | | |

1) Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm² (one layer, 70µm thick) copper area for drain connection. PCB is vertical in still air.

2) See figure 3 for more detailed information

3 Thermal characteristics

Table 3 Thermal characteristics

| Parameter | Symbol | Values | | | Unit | Note / Test Condition |
|-------------------------------------|------------|--------|------|------|------|--|
| | | Min. | Typ. | Max. | | |
| Thermal resistance, junction - case | R_{thJC} | - | - | 1.6 | K/W | top |
| | | - | 1 | - | | bottom |
| Device on PCB | R_{thJA} | - | - | 45 | | 6 cm ² cooling area ¹⁾ |

1) Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm² (one layer, 70µ, thick) copper area for drain connecton. PCB is vertical in still air.

4 Electrical characteristics

Electrical characteristics, at $T_J=25\text{ °C}$, unless otherwise specified.

Table 4 Static characteristics

| Parameter | Symbol | Values | | | Unit | Note / Test Condition |
|----------------------------------|---------------|--------|------|------|---------------|--|
| | | Min. | Typ. | Max. | | |
| Drain-source breakdown voltage | $V_{(BR)DSS}$ | 150 | - | - | V | $V_{GS}=0\text{ V}$, $I_D=1.0\text{ mA}$ |
| Gate threshold voltage | $V_{GS(th)}$ | 2 | 3 | 4 | | $V_{DS}=V_{GS}$, $I_D=110\text{ }\mu\text{A}$ |
| Zero gate voltage drain current | I_{DSS} | - | 0.1 | 10 | μA | $V_{DS}=120\text{ V}$, $V_{GS}=0\text{ V}$, $T_J=25\text{ °C}$ |
| | | - | 10 | 100 | | $V_{DS}=120\text{ V}$, $V_{GS}=0\text{ V}$, $T_J=125\text{ °C}$ |
| Gate-source leakage current | I_{GSS} | - | 10 | 100 | nA | $V_{GS}=20\text{ V}$, $V_{DS}=0\text{ V}$ |
| Drain-source on-state resistance | $R_{DS(on)}$ | - | 13.1 | 16.5 | m Ω | $V_{GS}=10\text{ V}$, $I_D=30\text{ A}$ |
| | | - | 14 | 17.9 | | $V_{GS}=8\text{ V}$, $I_D=15\text{ A}$ |
| Gate resistance | R_G | - | 0.7 | - | Ω | |
| Transconductance | g_{fs} | 24 | 48 | - | S | $ V_{DS} > 2 I_D R_{DS(on)max}$, $I_D=30\text{ A}$ |

Table 5 Dynamic characteristics

| Parameter | Symbol | Values | | | Unit | Note / Test Condition |
|------------------------------|--------------|--------|------|------|------|--|
| | | Min. | Typ. | Max. | | |
| Input capacitance | C_{iss} | - | 2100 | 2800 | pF | $V_{GS}=0\text{ V}$, $V_{DS}=75\text{ V}$, $f=1\text{ MHz}$ |
| Output capacitance | C_{oss} | - | 240 | 320 | | |
| Reverse transfer capacitance | C_{riss} | - | 5 | - | | |
| Turn-on delay time | $t_{d(on)}$ | - | 10 | - | ns | $V_{DD}=75\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=30\text{ A}$, $R_G=1.6\text{ }\Omega$ |
| Rise time | t_r | - | 10 | - | | |
| Turn-off delay time | $t_{d(off)}$ | - | 17 | - | | |
| Fall time | t_f | - | 7 | - | | |

Table 6 Gate charge characteristics¹⁾

| Parameter | Symbol | Values | | | Unit | Note / Test Condition |
|-----------------------|---------------|--------|------|------|------|---|
| | | Min. | Typ. | Max. | | |
| Gate to source charge | Q_{gs} | - | 11 | - | nC | $V_{DD}=75\text{ V}$, $I_D=30\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$ |
| Gate to drain charge | Q_{gd} | - | 4 | - | | |
| Switching charge | Q_{sw} | - | 12 | - | | |
| Gate charge total | Q_g | - | 26 | 35 | | |
| Gate plateau voltage | $V_{plateau}$ | - | 5.2 | - | V | |
| Output charge | Q_{oss} | - | 68 | 90 | | $V_{DD}=75\text{ V}$, $V_{GS}=0\text{ V}$ |

1) See figure 16 for gate charge parameter definition

Table 7 Reverse diode characteristics

| Parameter | Symbol | Values | | | Unit | Note / Test Condition |
|----------------------------------|---------------|--------|------|------|------|---|
| | | Min. | Typ. | Max. | | |
| Diode continuous forward current | I_s | - | - | 45 | A | $T_C=25\text{ °C}$ |
| Diode pulse current | $I_{S,pulse}$ | - | - | 180 | | |
| Diode forward voltage | V_{SD} | - | 0.9 | 1.2 | V | $V_{GS}=0\text{ V}$, $I_F=45\text{ A}$, $T_j=25\text{ °C}$ |
| Reverse recovery time | t_{rr} | - | 110 | - | ns | $V_R=75\text{ V}$, $I_F=30\text{ A}$, |
| Reverse recovery charge | Q_{rr} | - | 337 | - | nC | $di_F/dt=100\text{ A}/\mu\text{s}$ |

5 Electrical characteristics diagrams

Table 8

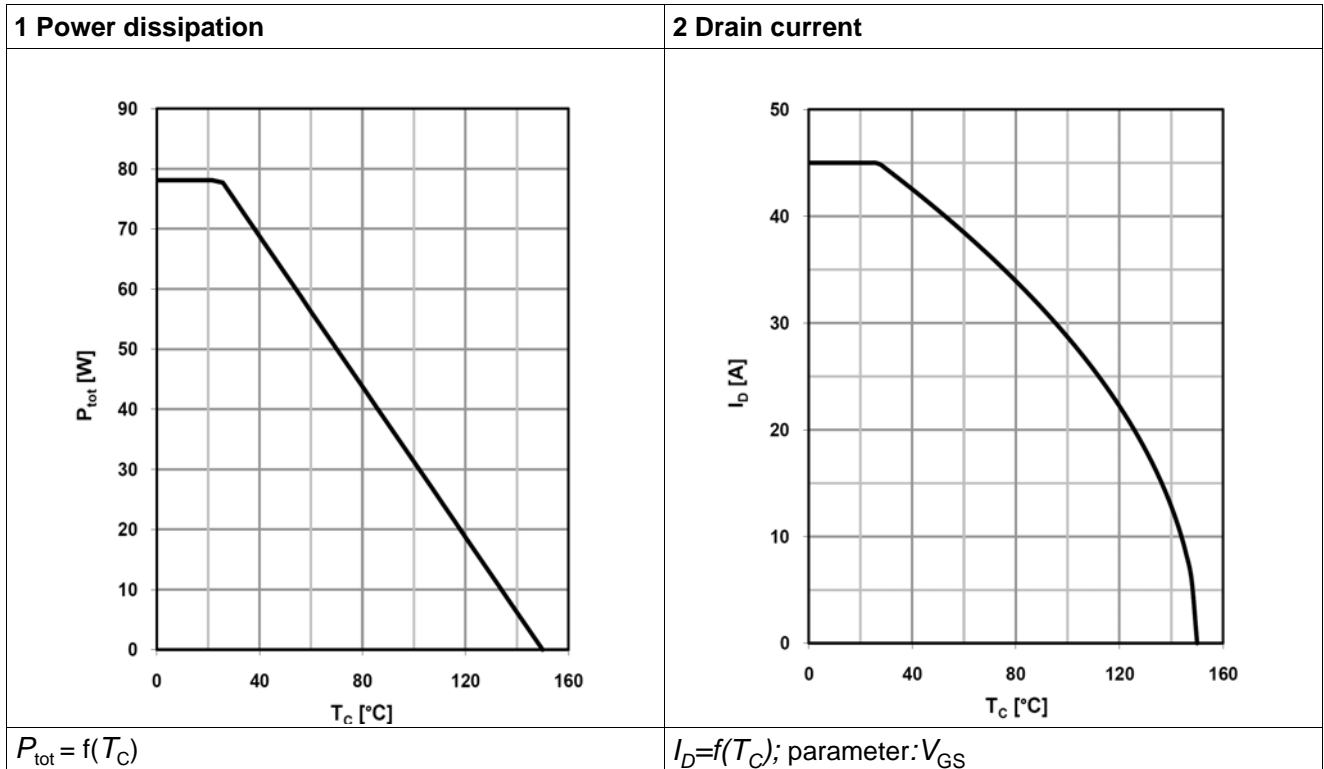


Table 9

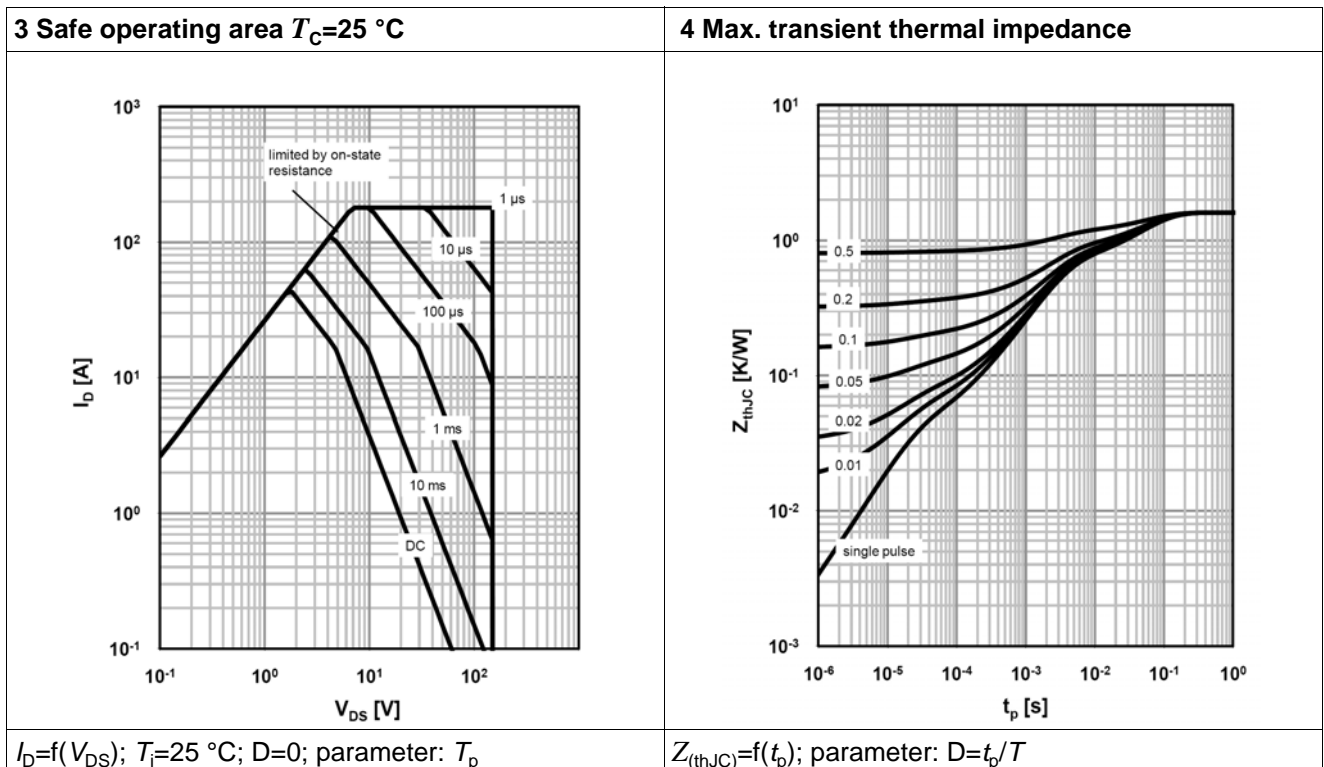


Table 10

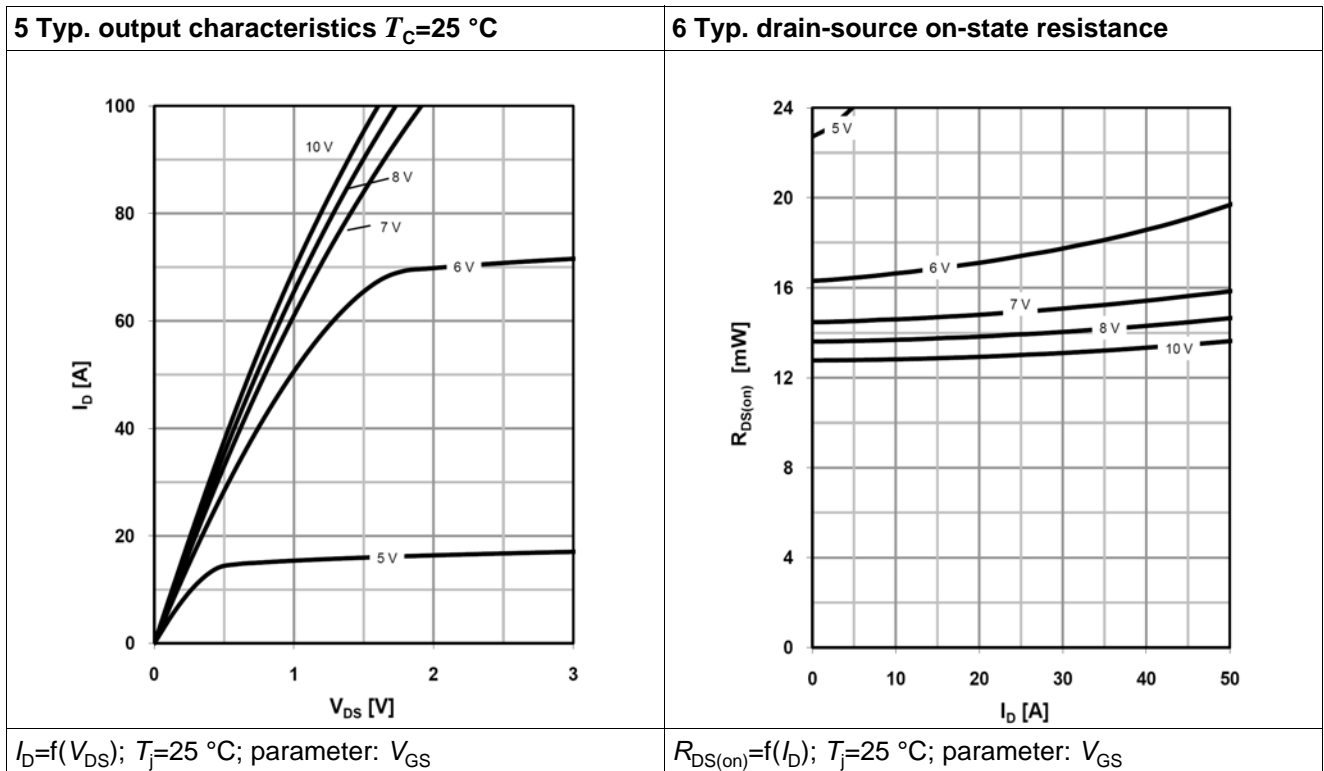


Table 11

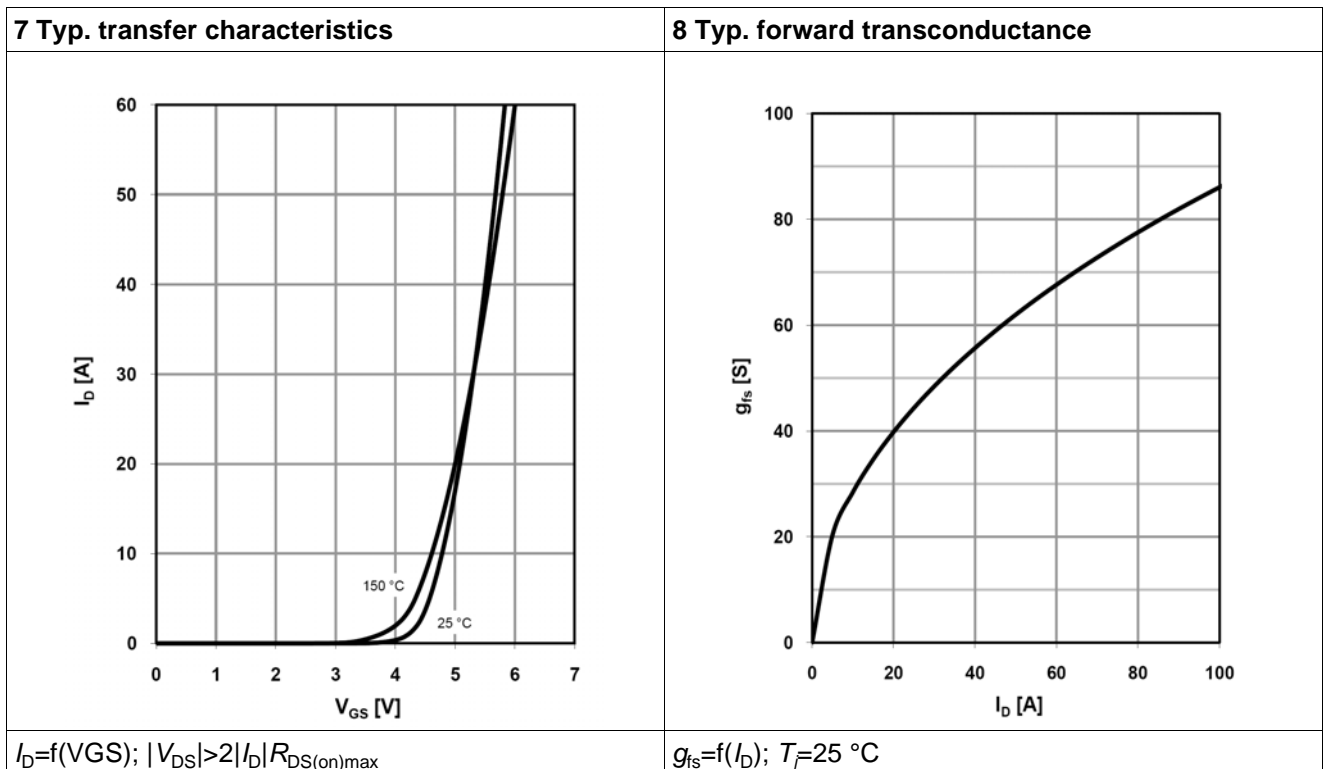


Table 12

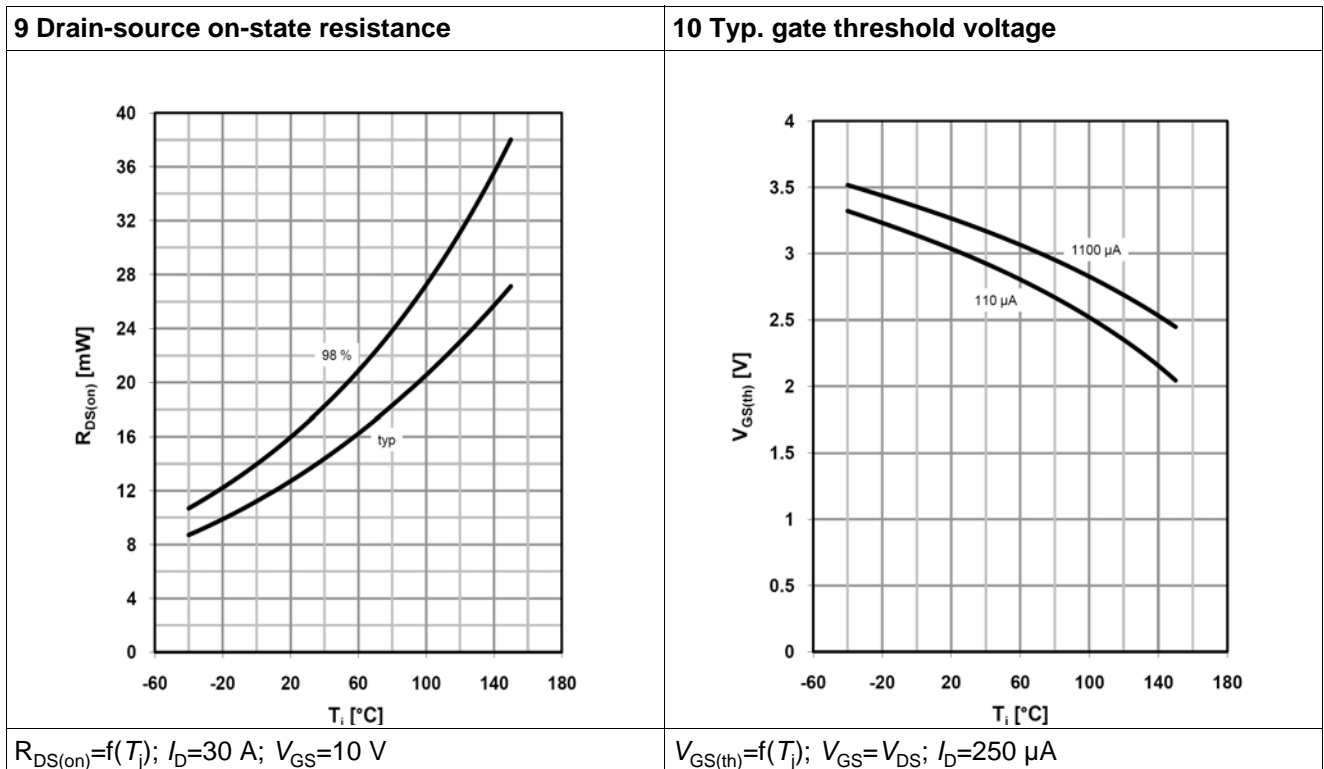


Table 13

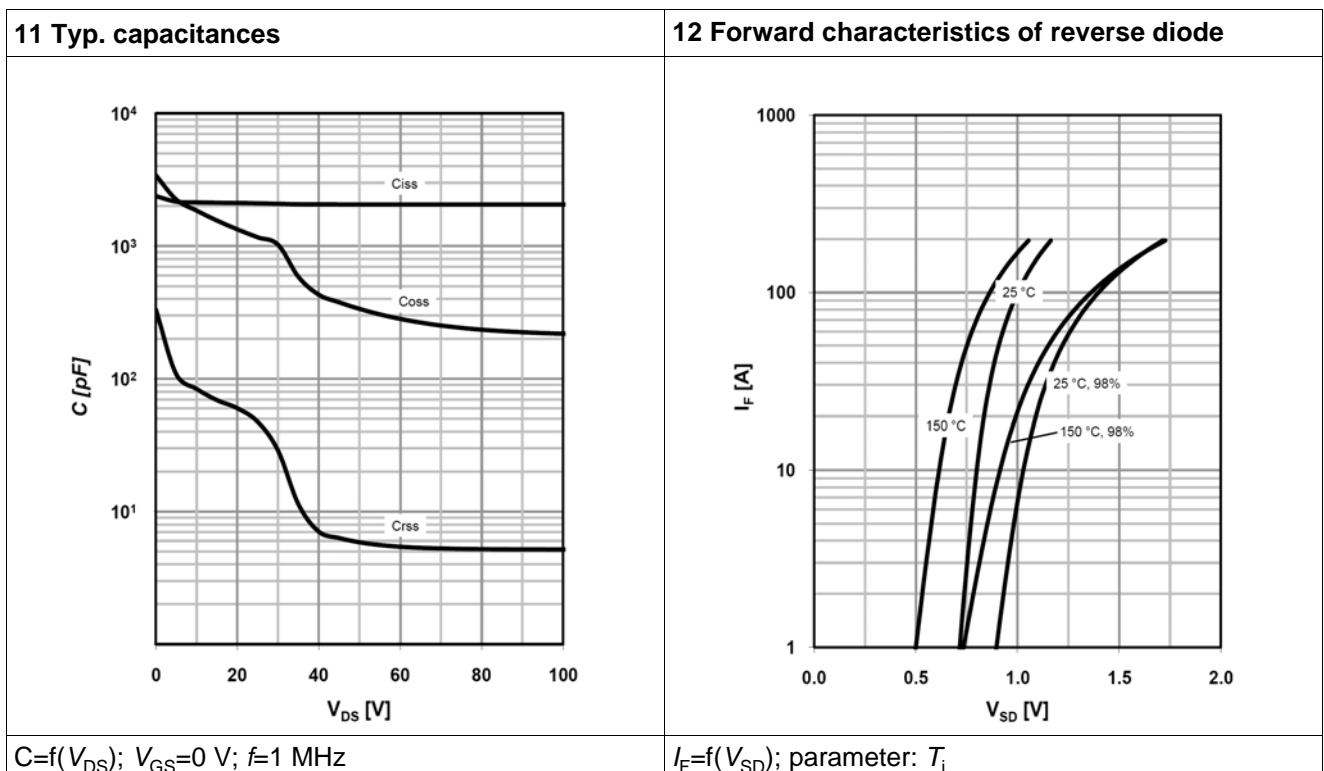


Table 14

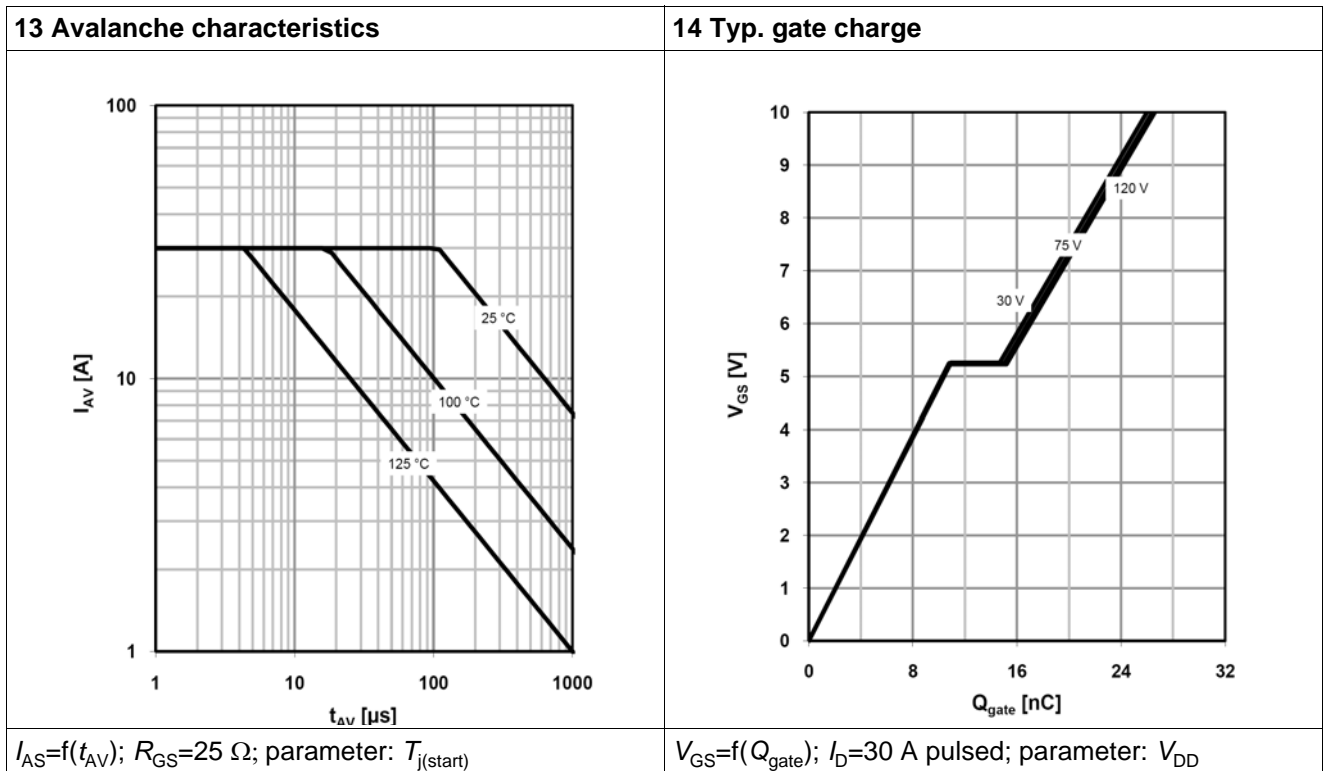
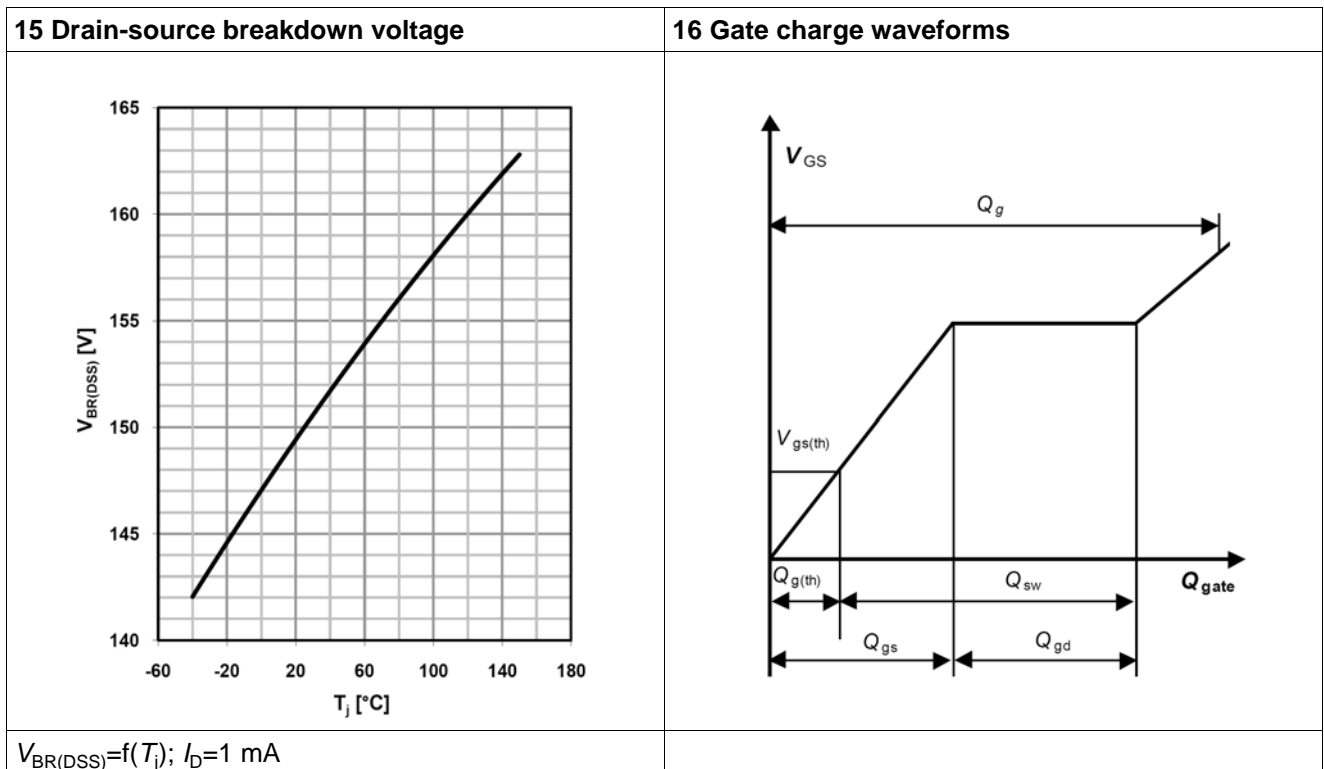


Table 15



6 Package outlines

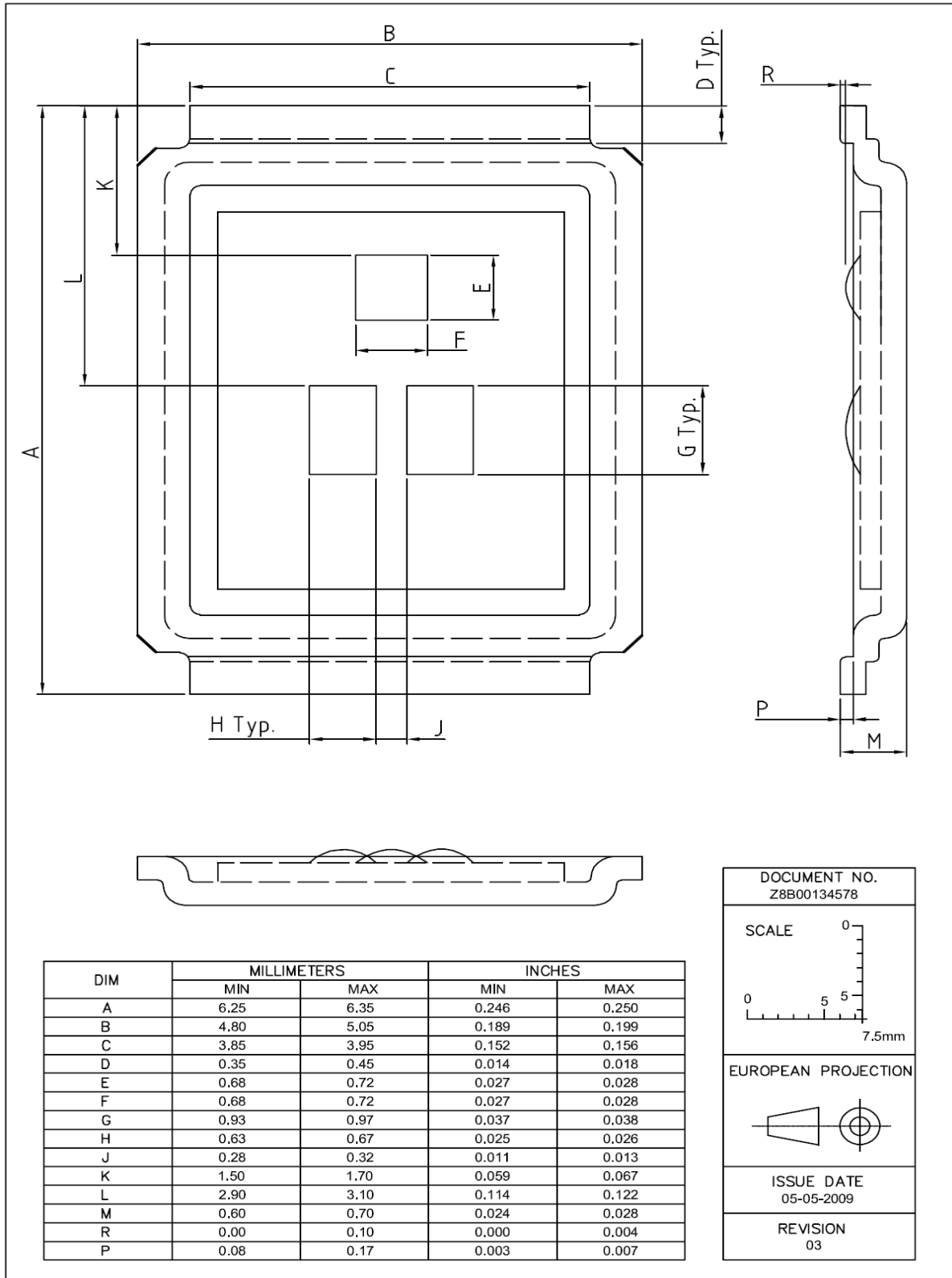


Figure 1 Outlines MG-WDSO-2, dimensions in mm/inches

7 Package outlines

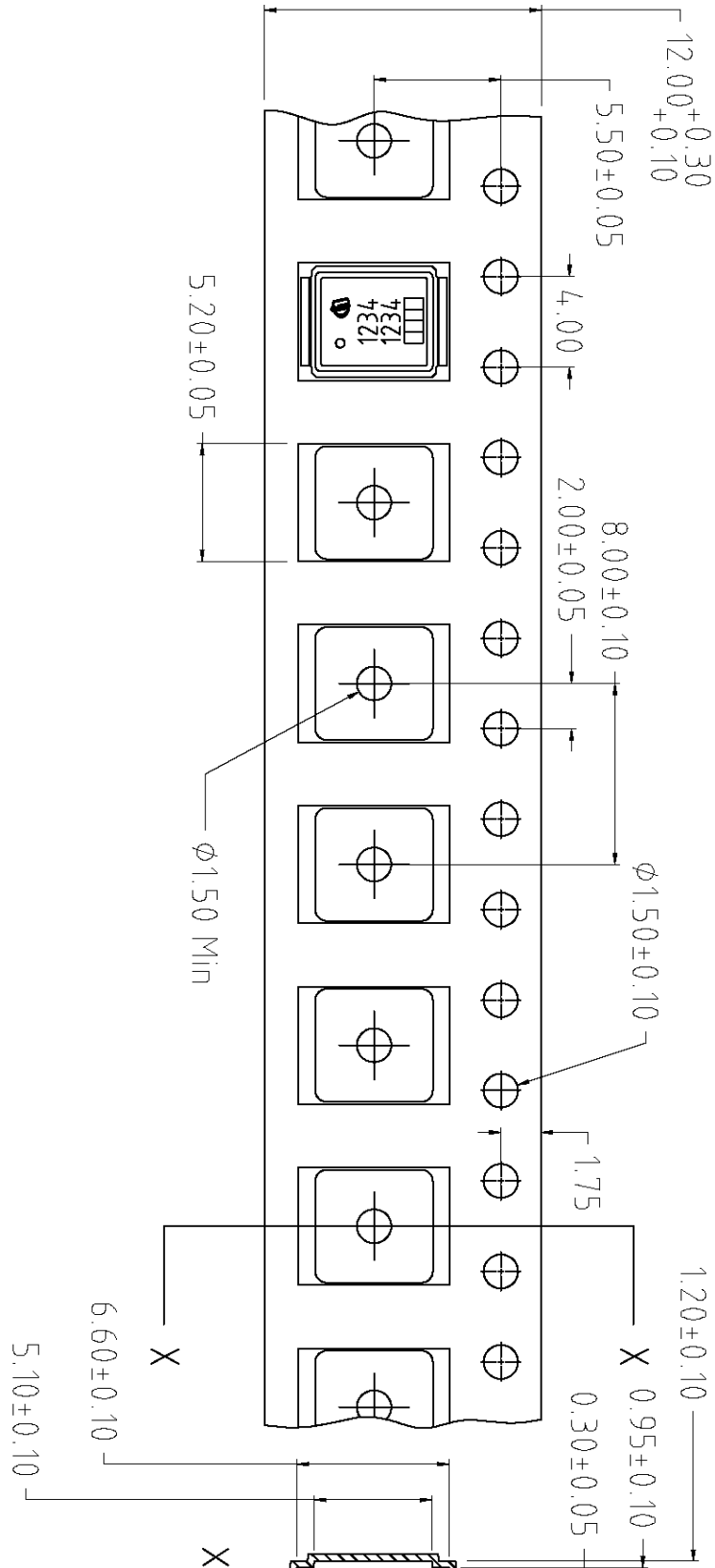


Figure 2 Outlines MG-WDSO-2, dimensions in mm/inches

8 Package outlines

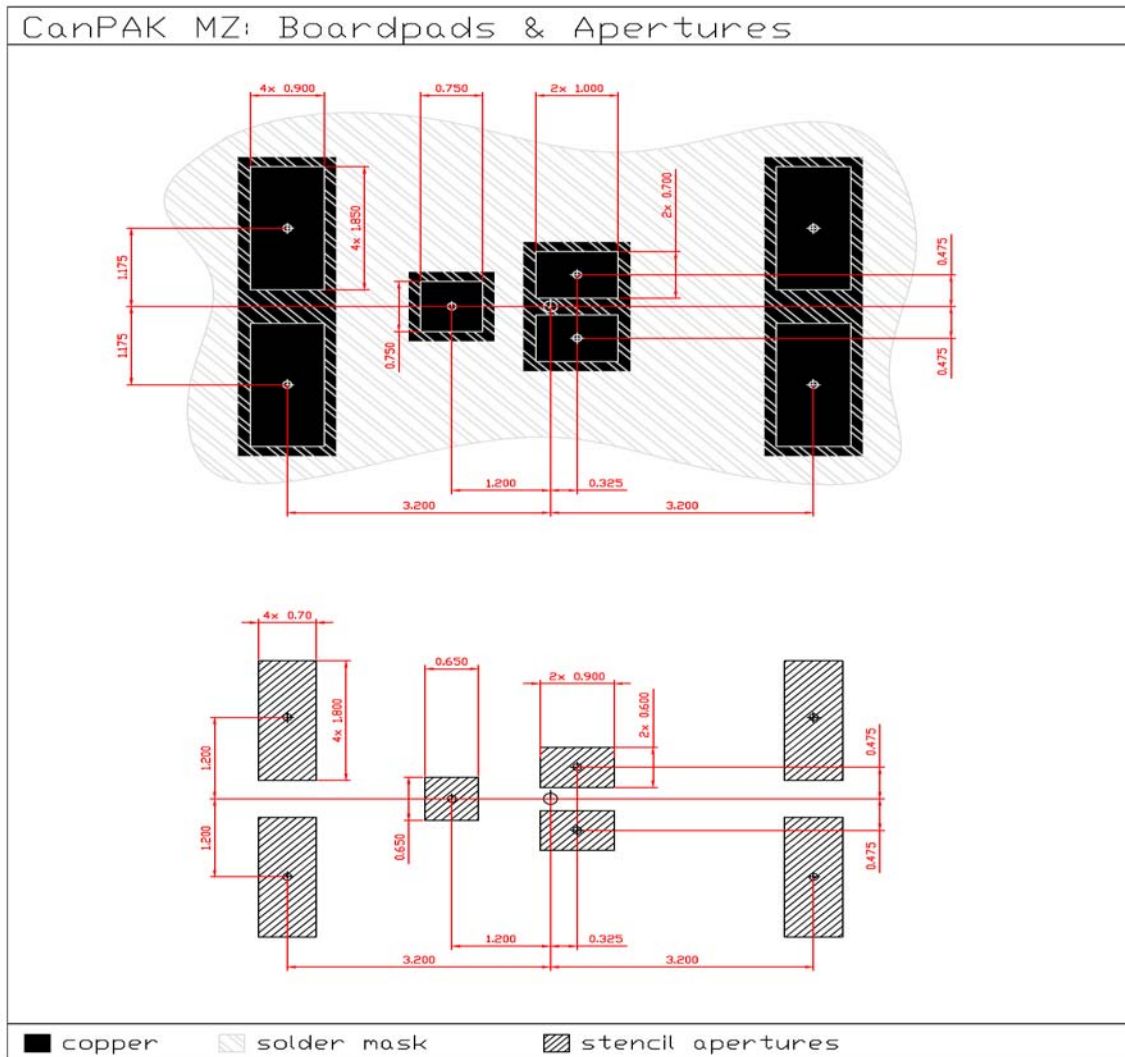
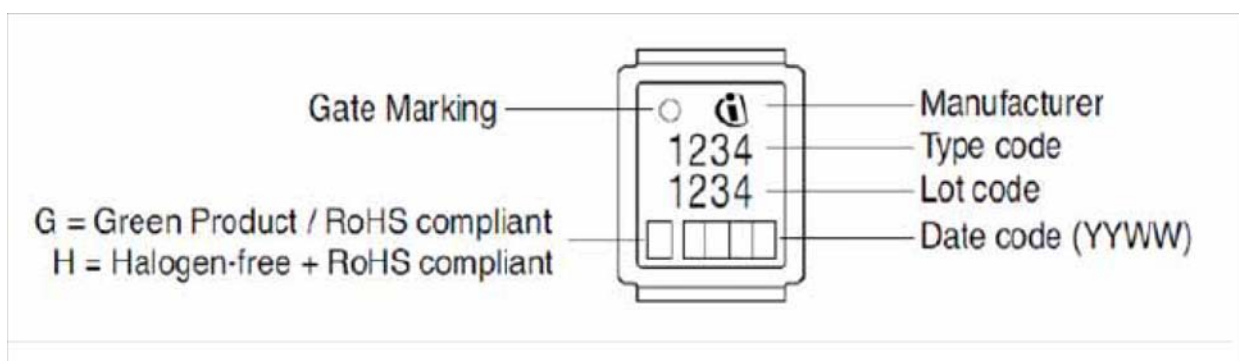


Figure 3 Outlines MG-WDSO-2, dimensions in mm/inches

9 Marking layout



9 Revision History

Revision History: 2011-07-20, 2.1

Previous Revision:

| Revision | Subjects (major changes since last revision) |
|----------|--|
| 0.1 | Release of target data sheet |
| 2.0 | Release Final version |
| 2.2 | Insert Marking layout |
| | |

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